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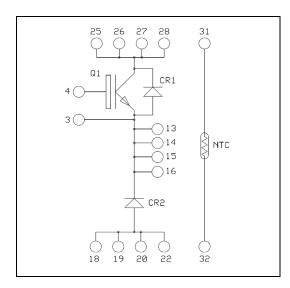


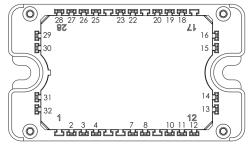


Buck chopper High speed IGBT 5 Power Module

$$V_{CES} = 650V$$

 $I_{C} = 200A$ @ $Tc = 25$ °C





Pins 25/26/27/28 ; 13/14/15/16 ; 18/19/20/22 must be shorted together

Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- High speed IGBT 5
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 100 kHz
 - Low leakage current
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

All ratings @ $T_i = 25$ °C unless otherwise specified

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Voltage		650	V
Ţ	Continuous Collector Current	$T_C = 25^{\circ}C$	200	
I_{C}		$T_C = 80$ °C	120	Α
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	400	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Power Dissipation		483	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.



Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 650V$				200	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.65	2.2	V
$V_{CE(sat)}$		$I_{\rm C} = 200 {\rm A}$ $T_{\rm j} = 150 {\rm °C}$		1.9		v	
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 2mA$		3.3	4.0	4.7	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				480	nA

Dynamic Characteristics

•	Channet windin	_	M:	T	M	¥734	
	Characteristic	Test Conditions	3	Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			12		
C_{oes}	Output Capacitance	$V_{CE} = 25V$			0.2		nF
C_{res}	Reverse Transfer Capacitance	f = 1MHz			0.044		
Q_{G}	Gate charge	$V_{GE} = 15V, I_{C} = V_{CE} = 520V$	$V_{GE} = 15V, I_{C} = 200A$ $V_{CE} = 520V$		480		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	hing (25°C)		21		ns
$T_{\rm r}$	Rise Time	$V_{GE} = 15V$			15		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 400V$ $I_{C} = 100A$			180		
$T_{\rm f}$	Fall Time	$R_G = 1\Omega$		18			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = 15V$ $V_{Bus} = 400V$ $I_{C} = 100A$			20		ns
$T_{\rm r}$	Rise Time				15		
T _{d(off)}	Turn-off Delay Time				205		
T_{f}	Fall Time	$R_G = 1\Omega$			26		
Eon	Turn on Energy	$V_{GE} = 15V$ $V_{Bus} = 400V$ $I_{C} = 100A$ $R_{G} = 1\Omega$	$T_j = 150$ °C		3		m I
E_{off}	Turn off Energy		$T_j = 150$ °C		1.2		mJ
R_{Gint}	Integrated gate resistor				1.25		Ω
R_{thJC}	Junction to Case Thermal Resistance					0.31	°C/W

Diode ratings and characteristics (per diode)

Symbol	Characteristic Test Conditions		Min	Typ	Max	Unit	
V_{RRM}	Peak Repetitive Reverse Voltage					650	V
I_{RM}	Reverse Leakage Current	$V_R=650V$				200	μΑ
I_F	DC Forward Current		$Tc = 25^{\circ}C$		200		A
V	Diode Forward Voltage	$I_F = 200A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$		1.6	2.2	V
V_{F}		$V_{GE} = 0V$	$T_{i} = 150^{\circ}C$		1.65		V
t_{rr}	Reverse Recovery Time	$I_{\rm F} = 100 A$	$T_j = 25$ °C		46		ns
ι _{rr}	Reverse Recovery Time		$I_F = 100A$ $V_R = 400V$ $T_j = 150^{\circ}C$	$T_{\rm j} = 150^{\circ}{\rm C}$		62	
	O _{rr} Reverse Recovery Charge di/dt =6000A/μs	rse Recovery Charge $\frac{di}{dt} = 6000 A/\mu s$ $\frac{T_j = 25^\circ}{dt}$	$T_j = 25^{\circ}C$		2		
Ųп			$T_j = 150$ °C		4		μC
R_{thJC}	Junction to Case Thermal Resistance	•				0.35	°C/W



Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

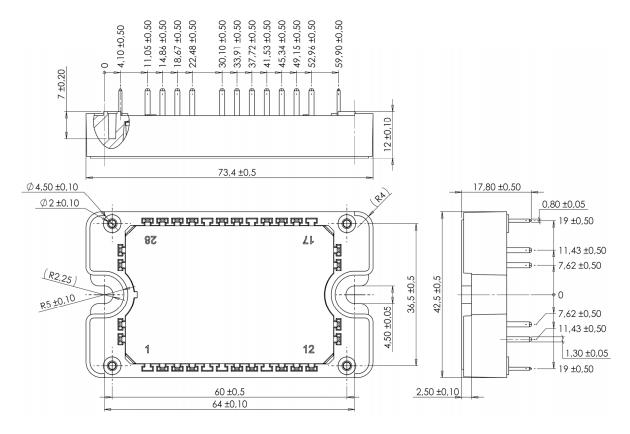
Symbol	Characteristic		Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta \mathrm{B/B}$		$T_{\rm C} = 100^{\circ}{\rm C}$		4		%

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$
 R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000		V
T_{J}	Operating junction temperature range			-40	175	
T_{JOP}	Recommended junction temperature under sy	witching condit	ions	-40	T _J max -25	°C
T_{STG}	Storage Temperature Range			-40	125	
$T_{\rm C}$	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

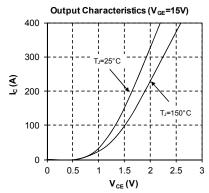
Package outline (dimensions in mm)

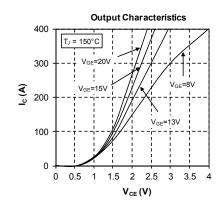


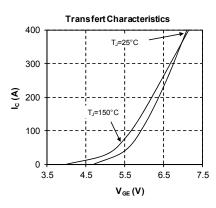
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

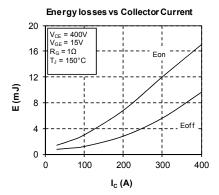


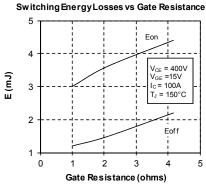
Typical performance curve

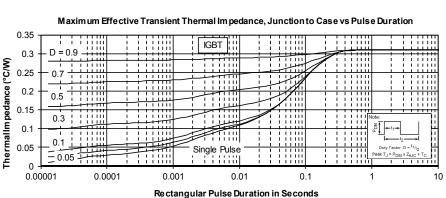






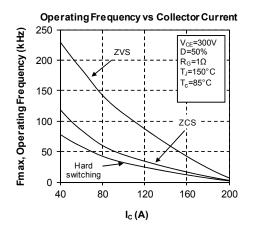


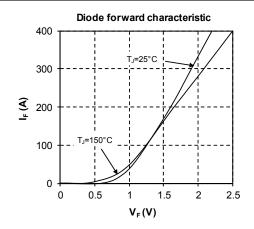




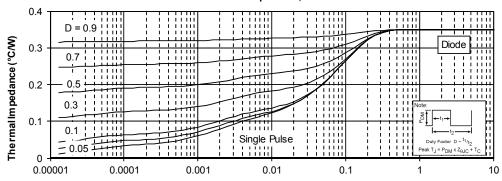


Power Matters.™





Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



Rectangular Pulse Duration in Seconds



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